

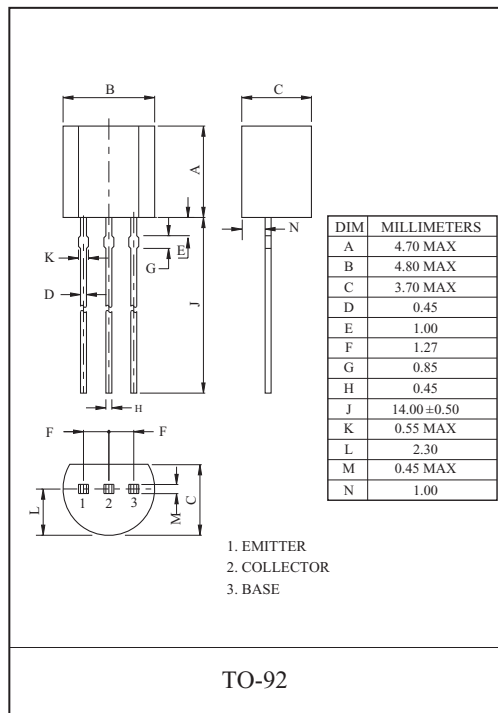
GENERAL PURPOSE APPLICATION.
HIGH VOLTAGE APPLICATION.

FEATURES

- High Collector Breakdown Voltage
: $V_{CBO}=-160V$, $V_{CEO}=-150V$
- Low Leakage Current.
: $I_{CBO}=-50nA(\text{Max.}) @V_{CB}=-120V$
- Low Saturation Voltage
: $V_{CE(\text{sat})}=-0.5V(\text{Max.}) @I_C=-50mA, I_B=-5mA$
- Low Noise : $NF=8dB(\text{Max.})$

MAXIMUM RATING (Ta=25 °C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-160	V
Collector-Emitter Voltage	V_{CEO}	-150	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-600	mA
Base Current	I_B	-100	mA
Collector Power Dissipation (Ta=25 °C)	P_C	625	mW
Collector Power Dissipation (Tc=25 °C)	P_C	1.5	W
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55 ~ 150	°C



2N5401C

ELECTRICAL CHARACTERISTICS (Ta=25 °C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB}=-120V, I_E=0$	-	-	-50	nA
		$V_{CB}=-120V, I_E=0, T_a=100^\circ C$	-	-	-50	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=-3V, I_C=0$	-	-	-50	nA
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=-0.1mA, I_E=0$	-160	-	-	V
Collector-Emitter Breakdown Voltage *	$V_{(BR)CEO}$	$I_C=-1mA, I_B=0$	-150	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=-10\mu A, I_C=0$	-5	-	-	V
DC Current Gain *	$h_{FE}(1)$	$V_{CE}=-5V, I_C=-1mA$	50	-	-	
		$V_{CE}=-5V, I_C=-10mA$	60	-	240	
		$V_{CE}=-5V, I_C=-50mA$	50	-	-	
Collector-Emitter Saturation Voltage *	$V_{CE(sat)1}$	$I_C=-10mA, I_B=-1mA$	-	-	-0.2	V
		$I_C=-50mA, I_B=-5mA$	-	-	-0.5	
Base-Emitter Saturation Voltage *	$V_{BE(sat)1}$	$I_C=-10mA, I_B=-1mA$	-	-	-1.0	V
		$I_C=-50mA, I_B=-5mA$	-	-	-1.0	
Transition Frequency	f_T	$V_{CE}=-10V, I_C=-10mA, f=100MHz$	100	-	300	MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=-10V, I_E=0, f=1MHz$	-	-	6	pF
Small-Signal Current Gain	h_{fe}	$V_{CE}=-10V, I_C=-1mA, f=1kHz$	40	-	200	
Noise Figure	NF	$V_{CE}=-5V, I_C=-250\mu A$ $R_g=1k\Omega, f=10Hz\sim 15.7kHz$	-	-	8	dB

* Pulse Test : Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.